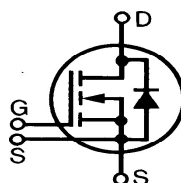


X2-Class HiPerFET™ Power MOSFET

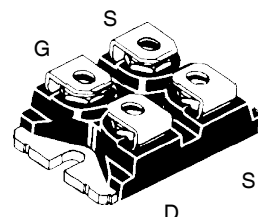
IXFN120N65X2

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 650V \\ I_{D25} &= 108A \\ R_{DS(on)} &\leq 24m\Omega \end{aligned}$$

miniBLOC, SOT-227
 E153432



G = Gate
S = Source
D = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	650	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	650	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	108	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	240	A
I_A	$T_C = 25^\circ\text{C}$	15	A
E_{AS}	$T_C = 25^\circ\text{C}$	3.5	J
P_D	$T_C = 25^\circ\text{C}$	890	W
dv/dt	$I_S \leq I_{DM}, V_{DD} \leq V_{DSS}, T_J \leq 150^\circ\text{C}$	50	V/ns
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ minute}$	2500 V~
	$I_{ISOL} \leq 1\text{mA}$	$t = 1 \text{ second}$	3000 V~
M_d	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
Weight		30	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 3\text{mA}$	650		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 8\text{mA}$	3.5		5.0 V
I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 5 mA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 60A$, Note 1			24 m Ω

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	V _{DS} = 10V, I _D = 60A, Note 1	46	76	S
R_{Gi}	Gate Input Resistance		0.74	Ω
C_{iss}	} V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		14	nF
C_{oss}			8700	pF
C_{rss}			5.5	pF
Effective Output Capacitance				
C_{o(er)}	Energy related	} V _{GS} = 0V V _{DS} = 0.8 • V _{DSS}	455	pF
C_{o(tr)}	Time related		1930	pF
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 60A R _G = 1Ω (External)		39	ns
t_r			26	ns
t_{d(off)}			82	ns
t_f			12	ns
Q_{g(on)}	} V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 60A		240	nC
Q_{gs}			87	nC
Q_{gd}			65	nC
R_{thJC}				0.14 °C/W
R_{thCS}			0.05	°C/W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			120 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			480 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 60\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		220	ns
Q_{RM}			2.3	μC
I_{RM}			21.0	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

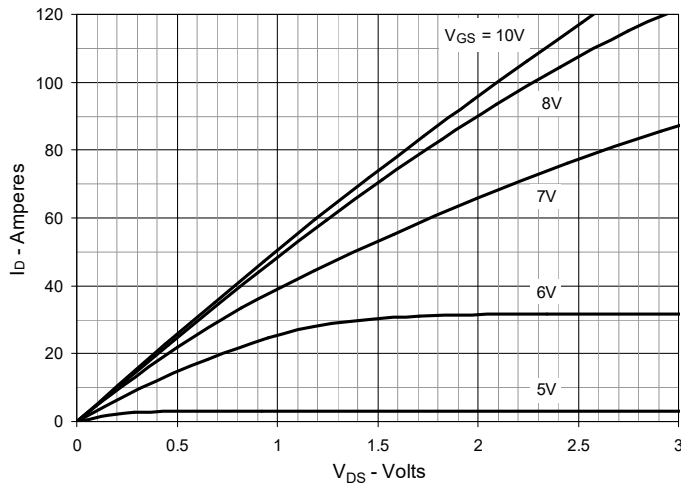


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

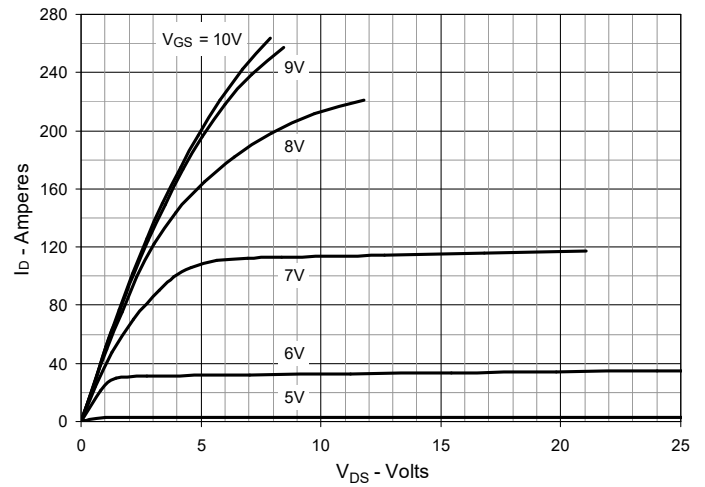


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

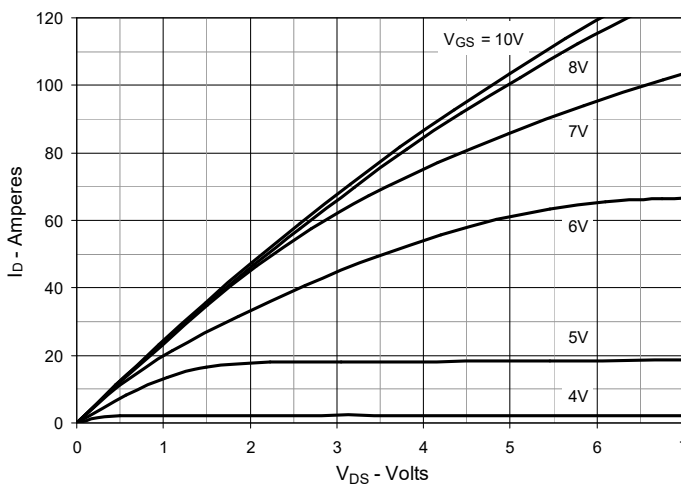


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 60\text{A}$ Value vs. Junction Temperature

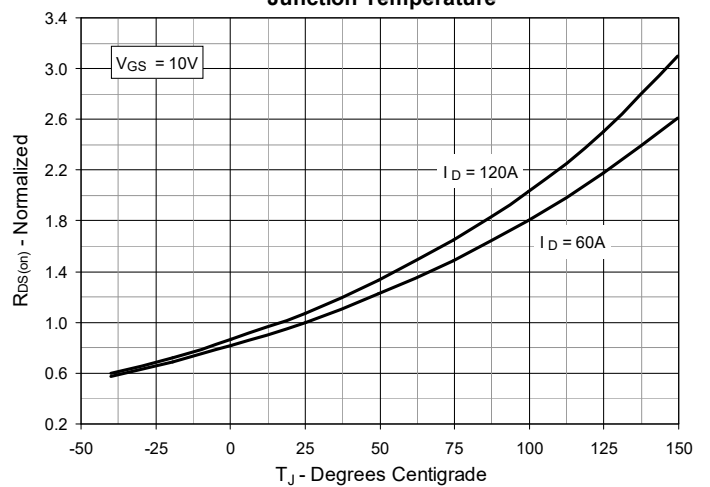


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 60\text{A}$ Value vs. Drain Current

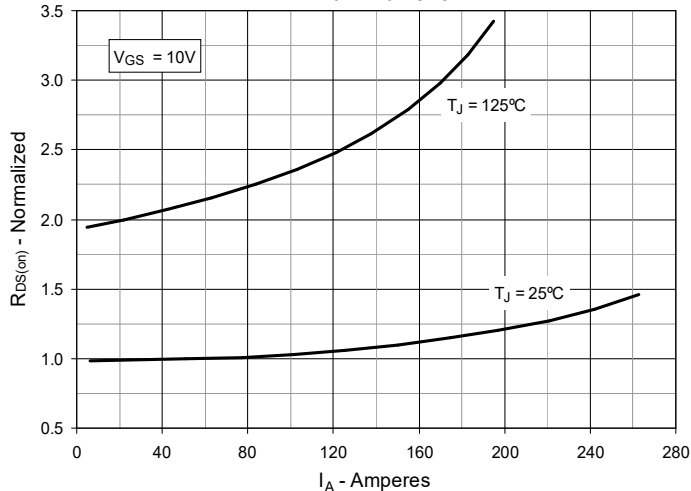


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

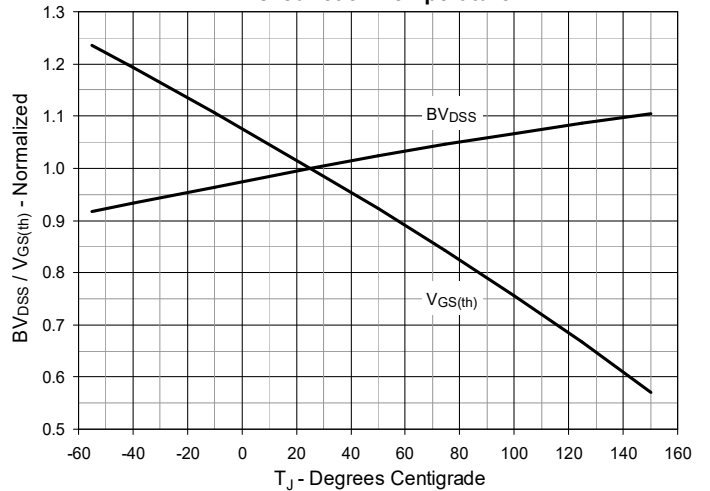


Fig. 7. Maximum Drain Current vs. Case Temperature

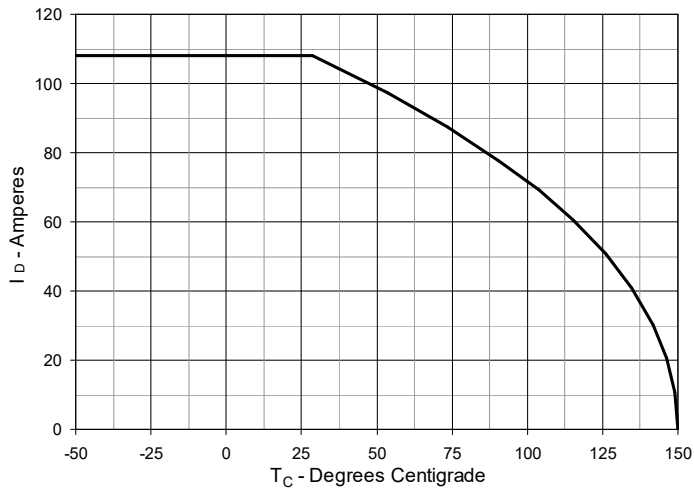


Fig. 8. Input Admittance

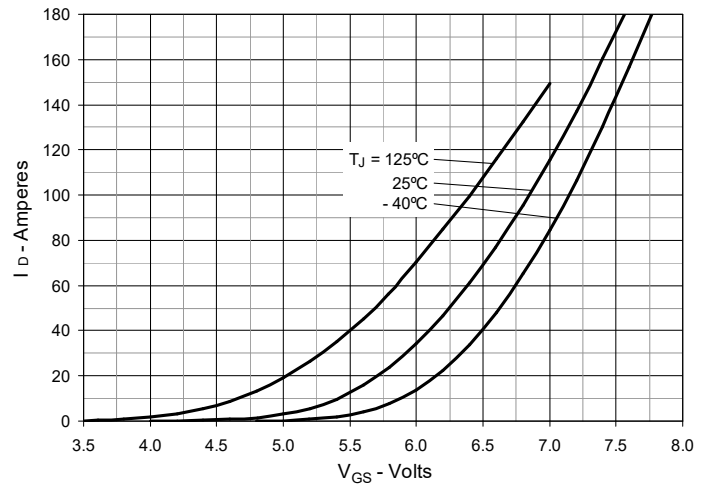


Fig. 9. Transconductance

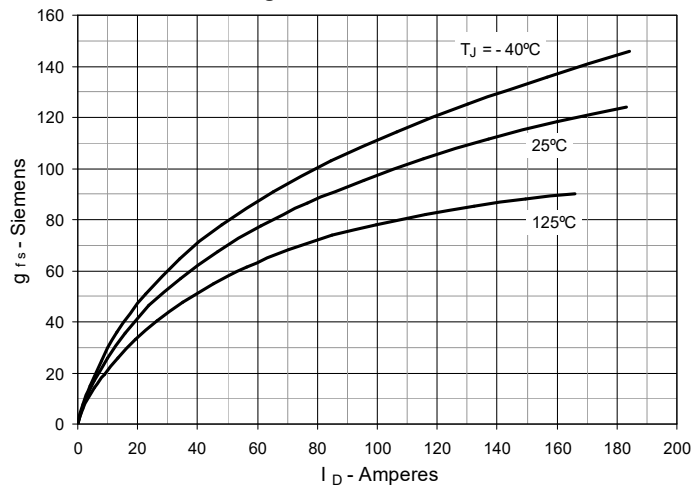


Fig. 10. Forward Voltage Drop of Intrinsic Diode

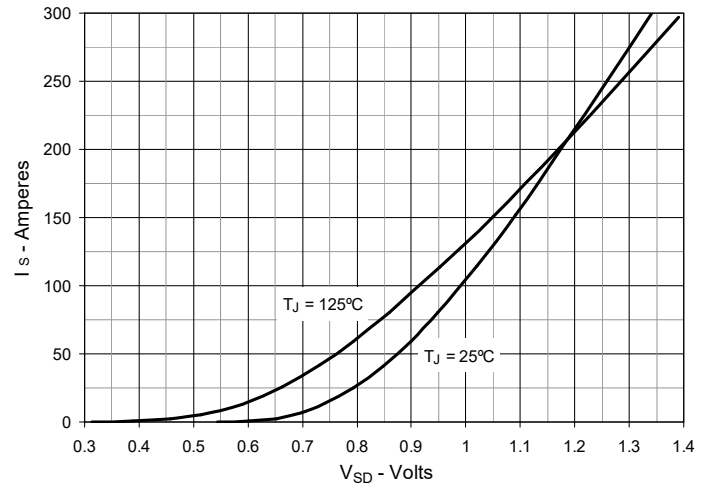


Fig. 11. Gate Charge

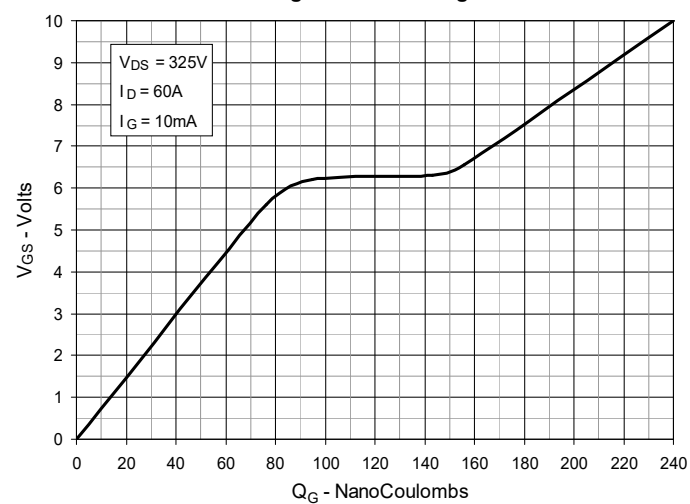


Fig. 12. Capacitance

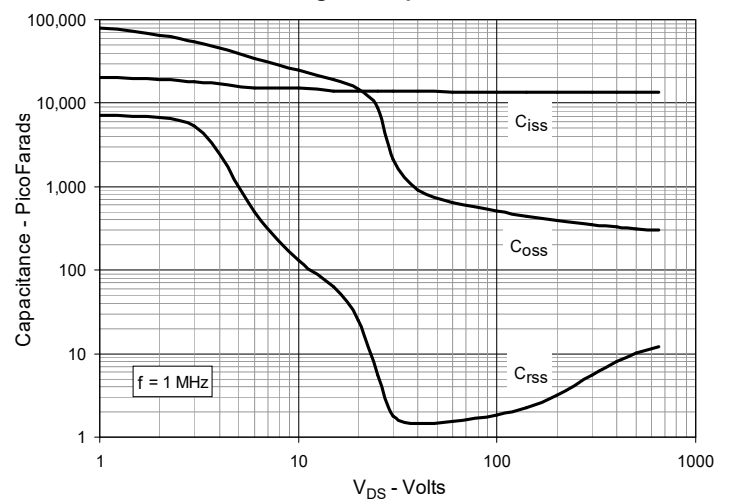
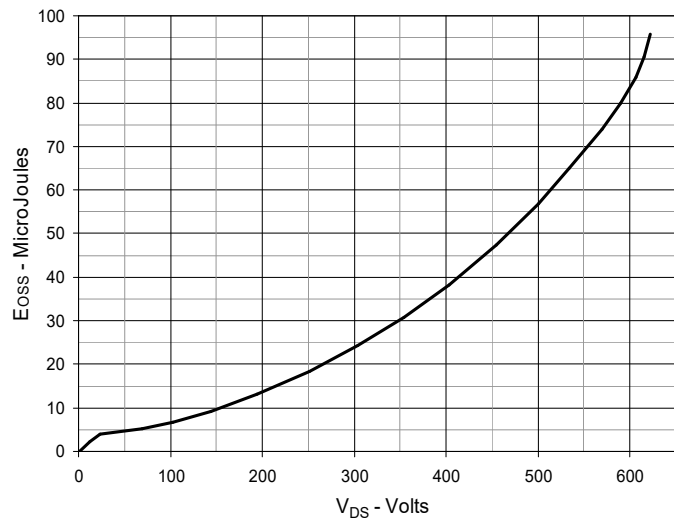
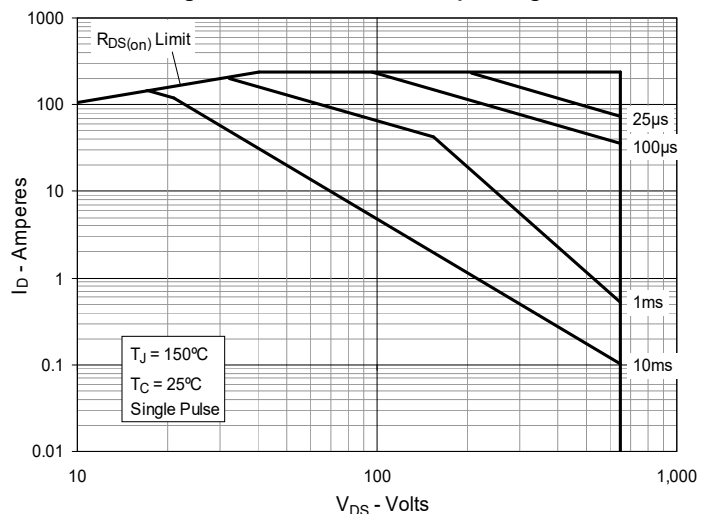
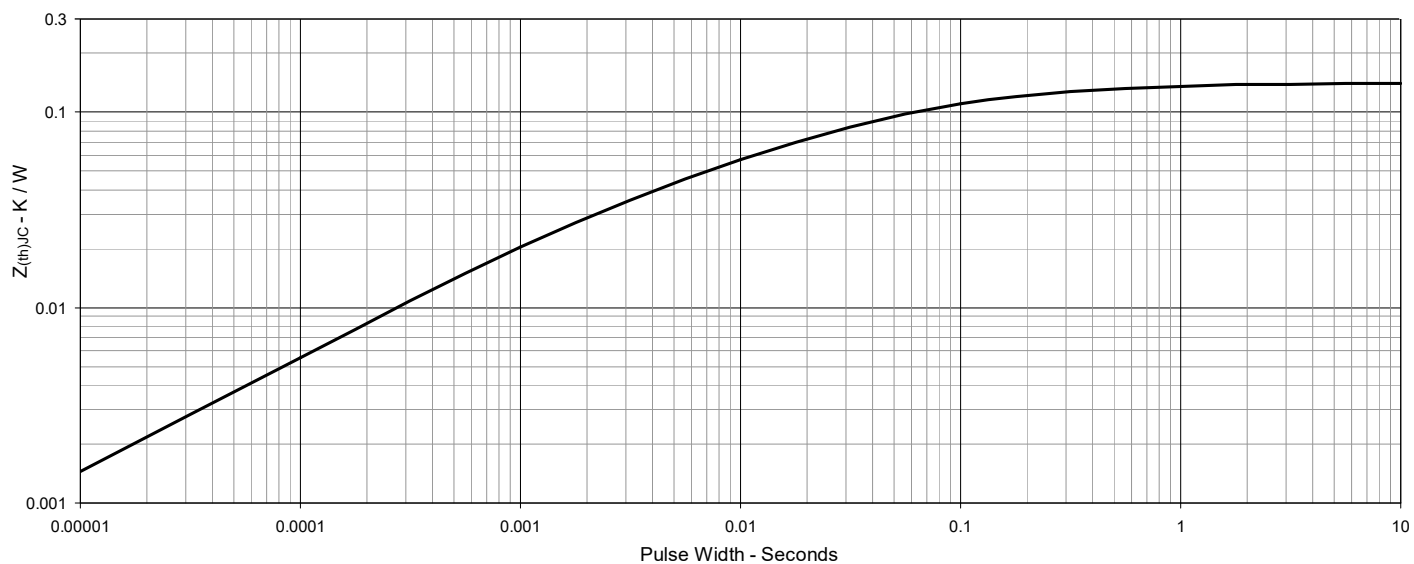
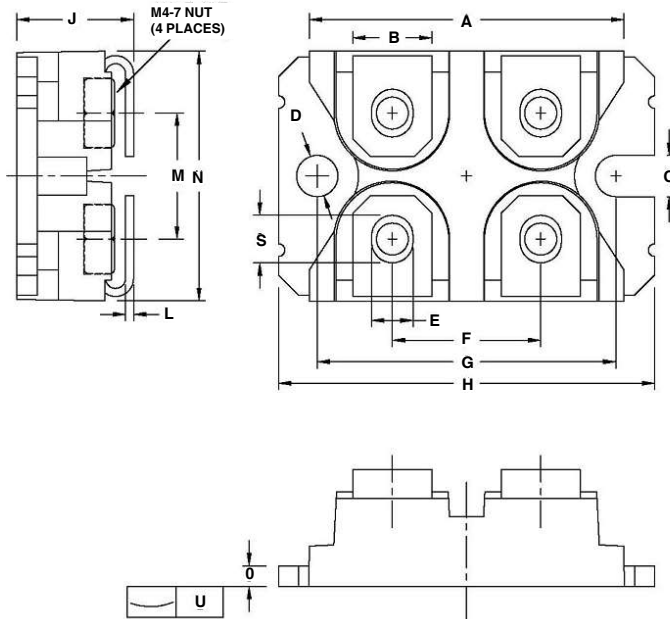


Fig. 13. Output Capacitance Stored Energy

Fig. 14. Forward-Bias Safe Operating Area

Fig. 15. Maximum Transient Thermal Impedance


SOT-227 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

- NUT MATERIAL:
STANDARD – Low carbon steel with Ni plating.
OPTIONAL: – Brass Nut is available.
PART NUMBER–BN
- ALL METAL SURFACE ARE PRE NI PLATED EXCEPT TRIM AREA.

